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msnoconf	authors	title	corrauthor
Mo-1-1i	R. Laskowski, N.E. Christensen	Free excitons in AlN under pressure	Laskowski
Mo-1-2i	P.J. Klar, J. Teubert, M. Güngerich, T. Niebling, W. Heimbrodtt,	High-pressure experiments on dilute nitride alloys	Klar
Mo-1-3i	G. Franssen	Hydrostatic pressure: a unique tool for the investigation of nitride light emitting structures	Franssen
Mo-1-4	T. Suski, G. Franssen, H. Teisseyre, L.H. Dmowski, J.A. Plesie	High pressure studies of radiative recombination mechanism in InN and In-rich InGaN	Suski
Mo-2-1	S.-H. Wei, Y.-H. Li, X.G. Gong	First-principles calculation of hydrostatic absolute deformation potentials and band offsets of semiconductors	Wei
Mo-2-2	S. Gilliland, J. Pellicer-Porres, A. Segura, A. Muñoz, P. Rodríguez	Electronic structure of CuAlO <sub>2</sub> and CuScO <sub>2</sub> delafossites under pressure	Gilliland
Mo-2-3	F. Rodríguez, F. Aguado, R. Valiente, M. Hanfland, J.P. Itié	Variation of the Jahn-Teller distortion with pressure in perovskite layers A <sub>2</sub> CuCl <sub>4</sub> . Influence on the Charge-Transfer band	Rodríguez
Mo-3-1i	A. Segura, D. Errandonea, D. Martínez-García, F.J. Manjón, A.	Transport measurements under pressure in III-IV layered semiconductors	Segura
Mo-3-2i	Amalia Patanè	The fragmented band structure of dilute Ga(AsN) alloys revealed by hydrostatic pressure and magnetic field	Patanè
Mo-4-1i	?????	????	Adams
Mo-4-2i	?????	????	Trzeciakowski
Mo-P1-1	A.H. Rodríguez, C.A. Duque, C. Trallero-Giner, G.J. Vázquez,	Effects of hydrostatic pressure on the optical transitions in self-assembled InAs/GaAs quantum lens with finite barrier	Hernández-Rodríguez
Mo-P1-2	A.S. Patel, K.M. Kesharwani	A Calculation On Pressure Induced Variation In Band Gap Energy of CuInTe <sub>2</sub> and CdSe	Kesharwani
Mo-P1-3	C. Kristukat, A.R. Goñi, K. Pötschke, D. Bimberg, C. Thomsen	Dependence of the band-gap pressure coefficients of self-assembled InAs/GaAs quantum dots on the dot size	Kristukat
Mo-P1-4	A.A. Lavrentyev, B.V. Gabrelian, B.B. Kulagin, I.Ya. Nikiforov, V	The influence of pressure on the electronic properties of semiconductor compounds ZnS, CuGaS <sub>2</sub> , and InPS <sub>4</sub>	Lavrentyev
Mo-P1-5	A. Nishikawa	Electronic structure of tellurium under high pressure	Nishikawa

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Mo-P1-6	P.S. Branício, J.P. Rino	Vibrational properties of InP under Pressure: A Molecular-Dynamics Study	Branício
Mo-P1-7	T. FUKUSHIMA, T. KUME, S. SASAKI, H. SHIMIZU, H. Fukuoka	High-Pressure Raman Study on Type I Germanium Clathrate	Kume
Mo-P1-8	M.P. Halsall, M.P. Jackson, M. Gungerich, P.J. Klar, W. Heimbach	Vibrational properties of GaP and GaP <sub>1-x</sub> N <sub>x</sub> under hydrostatic pressures up to 30 GPa	Jackson
Mo-P1-9	T. KUME, T. FUKUSHIMA, S. SASAKI, H. SHIMIZU, H. Fukuoka	Raman Study of Semiconductor Clathrates under High Pressure	Kume
Mo-P1-10	F.J. Manjón, D. Errandonea, N. Garro, A.H. Romero, J. Serrano	Lattice dynamics of AlN under pressure: Raman spectroscopy and ab initio calculations	Manjón
Mo-P1-11	P. Rodríguez-Hernández, A. Muñoz, J. Pellicer-Porres, D. Marti	Lattice dynamics of CuAlO <sub>2</sub> under high pressure from ab initio calculations	Rodríguez-Hernández
Mo-P1-12	H. Shimizu, T. KUME, Y. Narita, S. SASAKI, H. Fukuoka, S. Ya	High Pressure Raman Study on Two Modifications of BaAl <sub>2</sub> Si <sub>2</sub>	Kume
Mo-P1-13	A.G. Kontos, E. Stavrou, V. Malamos, Y.S. Raptis, C. Raptis	High pressure Raman study of DyPO <sub>4</sub> at room- and low-temperatures	Raptis
Mo-P1-14	A. Polian, J.C. Chervin, P. Munsch, C. Piquier, F. Demangeot	Raman scattering in III-V nitrides - the InN case	Polian
Mo-P1-15	D. Errandonea, D. Martínez-García, J. Ruiz-Fuertes, R. Lacom	Optical absorption of scheelite PbWO <sub>4</sub> at high pressure	Segura
Mo-P1-16	F.J. Manjón, A. Segura, M. Amboage, J. Pellicer-Porres, J. F. S	Structural and optical high-pressure study of spinel-type MnIn <sub>2</sub> S <sub>4</sub>	Manjón
Mo-P1-17	S. G. Pavlov, H.-W. Hübers, H. Riemann, N. V. Abrosimov, N. A	Stress-controlled phonon-impurity resonant interactions in terahertz silicon lasers	Pavlov
Mo-P1-18	J.S. Reparaz, A. R. Goñi, M.I. Alonso, M.N. Pérez-Paz, M.C. T	Photoluminescence of CdSe quantum dots with Zn <sub>0.11</sub> Cd <sub>0.26</sub> Mg <sub>0.63</sub> Se barriers under hydrostatic pressure	Reparaz
Mo-P1-19	J. A. Sans, A. Segura, D. Errandonea, D. Martinez-García, V. F	Optical and transport properties of heavily Ga-doped wurtzite and rock-salt ZnO under pressure	Sans
Mo-P1-20	J.A. Sans, M. Ruiz-Castillo, A. Segura, J.Martínez-Pastor, D.Fu	Pressure dependence of photoluminescence of InAs/InP self-assembled quantum wires	Segura
Mo-P1-21	A.G. Slivka, P.P. Guranich, V.S. Shusta, O.I. Gerzanich, I.Yu.	Optical properties of Sn(Zn,Cd) <sub>2</sub> P <sub>2</sub> S <sub>6</sub> ferroelectric semiconductor crystals under hydrostatic pressures	Slivka

Mo-P1-22	Y. Ishibashi, T. Kobayashi, A.D. Prins, J. Nakahara, M.A. Loure	Excitation and pressure effects on photoluminescence from dislocation engineered silicon material	Kobayashi
Mo-P1-23	H. Teisseyre, A. Cros, D. Errandonea, A. Khapuridze, S. Lepko	Pressure behavior of the photoluminescence from GaN/AlGaIn quantum well grown on bulk GaN substrate along the polar and nonpolar direction	Grzegory
Mo-P1-24	A. Villasmil, J. Marquina, Ch.Power, J.González	Optical absorption and phase transitions in CdIn <sub>2</sub> S <sub>4</sub> spinel semiconductor at high pressure	González
Mo-P1-25	V.D. Blank, S.G. Buga, S.A. Terentiev, M.S. Kuznetsov, S.A. N	Electrical conductivity of heavily boron doped diamond single crystals grown by high-pressure-high-temperature method	Buga
Mo-P1-26	G. Franssen, J.A. Plesiewicz, L.H. Dmowski, P. Prystawko, W.	Influence of hydrostatic pressure on interface charge in AlGaIn/GaN heterostructures	Franssen
Mo-P1-27	K. M. Kesharwani, R. Kumar	Effects of pressure on electrical properties of amorphous silicon	Kesharwani
Mo-P1-28	A.S. Patel, K.M. Kesharwani	A Theoretical Study of Band gap and electrical resistivity of FeS <sub>2</sub> -Pyrite at high pressures	Kesharwani
Mo-P1-29	V.V. Kolomoets, A.E. Gorin, G.V. Gromova, S.I. Budsuljak, V.M	Tensoresistivity Effects in High Uniaxially Strained p-Si and n-Si	Kolomoets
Mo-P1-30	N.Ya. Minina, E.V. Bogdanov, A.A. Ilievsky, A.V. Polyanskiy, W	Two-dimensional electrons at n-GaAs/AlGaAs heterointerface under uniaxial compression	Minina
Mo-P1-31	S. Kagoshima, R. Kondo, N. Matsushita, M. Higa, S.V. Ovsyan	Ultra-high-pressure effects in metalloorganics	Ovsyannikov
Mo-P1-32	S.V. Ovsyannikov, V.V. Shchennikov, A.N. Titov, Y. Uwatoko	Pressure-induced insulator-metal transition in the novel layer metalloorganic structure (CoC <sub>10</sub> H <sub>10</sub> ) <sub>0.25</sub> TiSe <sub>2</sub>	Ovsyannikov
Mo-P1-33	V.V. Shchennikov Jr, S.V. Ovsyannikov, V.V. Shchennikov, I.V	High-pressure thermopower of Si wafers implanted with hydrogen ions	Shchennikov, Jr
Mo-P1-34	G.V. Tikhomirova, A.N. Babushkin	Resistivity relaxation of ammonium halides near high-pressure induced phase transitions	Tikhomirova
Mo-P1-35	P. Adamiec, R. Bohdan, A. Bercha, F. Dybala, W. Trzeciakows	Threshold currents under pressure in InGaAsSb/AlGaAsSb laser diodes	Adamiec
Mo-P1-36	E.Condrea, A.Nicorici, A.Tudoschiuc, A.Grozav	Transport Properties of Uniaxial Stressed Bi Nanowires	Condrea
Mo-P1-37	A.S. Patel, K.M. Kesharwani	A Calculation On Pressure Induced Variation In Band Gap Energy of CuInTe <sub>2</sub> and CdSe	Kesharwani

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Mo-P1-38	M. I. Daunov, I. K. Kamilov, S. F. Gabibov	About the nature of "heavy" electrons in gapless and narrow-gap semiconductor p-CdHgTe	Daunov
Mo-P1-39	I.V. Antonova	Pressure related defect engineering for silicon-on-insulator-like structures produced by either oxygen or nitrogen ion implantation	Antonova
Mo-P1-40	V. Shapovalov, V. Dyakonov, P. Aleshkevych, A. Nabialek, K. D	Linear deformation effect on the SWR acoustic mode in the La 0.67Ca0.33MnO3 manganite film	Dyakonov
Mo-P1-41	J.W. González, A.H. Rodríguez, N. Porrás-Montenegro, C.A. D	Impurity related optical properties in rectangular-transversal section GaAs-Ga <sub>1-x</sub> Al <sub>x</sub> As quantum-well wires: Hydrostatic pressure and electric field effects	González
Mo-P1-42	E.P. Skipetrov, A.V. Golubev, N.A. Pichugin, A.A. Plastun, N.N	Resonant impurity states in PbTe-based alloys doped with gallium and chromium under pressure	Skipetrov
Mo-P1-43	J. Teubert, P.J. Klar, W. Heimbrod, V. Gottschalch, A. Lindsay	Effect of localized B states on the magneto-transport properties of n-type (B,Ga,In)As under hydrostatic pressure	Teubert
Mo-P1-44	M.I. Daunov, I.K. Kamilov, S.F. Gabibov	A quasi-gapless semiconductor at high pressures – a model of amorphous semiconductor	Daunov
Tu-5-1i	B. A. Weinstein	Raman scattering under pressure in nanoparticle systems: Mode coupling, confinement, and disorder	Weinstein
Tu-5-2	A. Bernardi, J.S. Reparaz, A.R. Goñi, M.I. Alonso, J.O. Ossó, M	Raman scattering of carbon-induced Ge dots under hydrostatic pressure	Bernardi
Tu-5-3	I.P. Marko, N.F. Masse, S.J. Sweeney, A.D. Andreev, A.R. Ada	Band gap dependence of the recombination processes in InAs/GaAs quantum dots studied using hydrostatic pressure	Marko
Tu-5-4	G.H. Li, F.H. Su, W.J. Wang, K. Ding, Y.F. Liu, W. Chen, A.G. L	Pressure Behavior of UV and Green Emissions in ZnO Micro-rods	Li
Tu-5-5	P.Y. Yu, I.-H. Choi	Coefficients of Optical Phonons by Resonant Raman Scattering	Yu
Tu-6-1i	D. Dunstan ?????	Strength of strained quantum wells and other small structures	Dunstan
Tu-6-2	A. Bernardi, P. Lacharmoise, A.R. Goñi, M.I. Alonso, P.O. Vacc	Strain storage in semiconductor micro-origami tubes: a study by Raman spectroscopy	Lacharmoise
Tu-6-3i	D.J. Paul	Towards a Si/SiGe quantum cascade laser?????	Paul
Tu-11-1	M.S. Kagan, I.V. Altukhov, S.K. Paprotskiy, V.P. Sinis, I.N. Yass	Carrier Injection as a Cause of THz Lasing Excitation in SiGe/Si QW Structures	Kagan

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Tu-7-1i	M. Hanfland	Structural studies at extreme pressures	Hanfland
Tu-7-2i	J.S. Tse	Superconductivity in high pressure SiH <sub>4</sub> and SnH <sub>4</sub>	Tse
Tu-7-3	Y. Mori, N. Niiya, T. Mizuno, T. Nishii, A. Fujii, Y. Fujii, J. Jiang,	Pressure-induced phase transition of Co-doped ZnO	Mori
Tu-7-4	J.P. Rino, P.S. Branício, F. Shimojo	Structural Phase Transformations in InP under Pressure: An ab initio and Molecular-Dynamics Study	Rino
Tu-P2-45	C.E.M. Campos, J.C. de Lima, T.A. Grandi, J.P. Itié, A. Polian,	Pressure-Induced Phase Transition of Zinc-Blende Semiconductors Produced by Mechanical Alloying	Campos
Tu-P2-46	U. Schwarz, D. Olguín, A. Cantarero, K. Syassen, H. Hanfland	Structural properties and electronic band structure of GaSe under pressure	Cantarero
Tu-P2-47	S. Singh, R. Chauhan	Structural Phase Transition in Transition Metal Compounds	Chauhan
Tu-P2-48	A. Perakis, D. Lampakis, Y.C. Boulmetis, C. Raptis	Second order ferroelastic phase transition in ZnF <sub>2</sub> at high-pressure studied by Raman spectroscopy	Raptis
Tu-P2-49	Y.C. Boulmetis, E. Stavrou, C. Raptis	Structural changes in amorphous chalcogenide semiconductors under high pressure: a Raman study	Raptis
Tu-P2-50	R.G. Jasinevicius, P.S. Pizani	On the ductile response dependence upon phase transformation in diamond turning of semiconductors	Jasinevicius
Tu-P2-51	D. Varshney, N. Kaurav, R. Kinge, K.K. Choudhary, R. K. Singh	Pressure dependence of elastic properties of InX (X = N, P, As): Role of charge transfer	Varshney
Tu-P2-52	D. Varshney, N. Kaurav, P. Sharma, K.K. Choudhary, R.K. Singh	High pressure structural phase transition in MgX (X = S, Se, Te) semiconducting compounds	Varshney
Tu-P2-53	A.G. Kontos, D. Lampakis, Y.S. Raptis, E. Liarokapis, Z.V. Popovic	Raman study of $\beta$ -Sr <sub>0.33</sub> V <sub>2</sub> O <sub>5</sub> micro-crystals under high pressure	Kontos
Tu-P2-54	R.S. Kumar, A.L. Cornelius, M.F. Nicol, M. Somayazulu, D. Errandonea	High Pressure Structure of Tb <sub>2</sub> Ti <sub>2</sub> O <sub>7</sub> Pyrochlore at Cryogenic Temperatures	Kumar
Tu-P2-55	J. López-Solano, P. Rodríguez-Hernández, S. Radescu, A. Muñoz	Theoretical study of tungstates under pressure	López-Solano
Tu-P2-56	Y. Mori, N. Niiya, T. Mizuno, T. Nishii, A. Fujii, Y. Fujii, K. Takarashi	Phase transition of b-FeSi <sub>2</sub> under high-pressure	Mori

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Tu-P2-57	J. López-Solano, A. Muñoz, A. Mujica	Structural phases of InAs under pressure	Mujica
Tu-P2-58	J. Pellicer-Porres, A. Segura, A.S. Gilliland, A. Polian, P. Munsch	Experimental and ab-initio equations of state of III-VI layered compounds: GaSe, InSe and GaS	Pellicer-Porres
Tu-P2-59	P.S. Pizani, M.R. Joya, R.G. Jasinevicius	High non-hydrostatic pressure-induced structural phase transitions of InSb probed by Raman scattering	Pizani
Tu-P2-60	T. Nishii, T. Mizuno, A. Fujii, Y. Fujii, Y. Mori, K. Takarabe, M. Imai	X-ray study of amorphous phase of BaSi <sub>2</sub> under high-pressure	Nishii
Tu-P2-61	V.V. Shchennikov, S.V. Ovsyannikov	Thermoelectric properties and phase transitions of II-VI semiconductors at ultrahigh pressure	Shchennikov
Tu-P2-62	S.V. Ovsyannikov, V.V. Shchennikov, A.Y. Manakov, A.Y. Likhachev	High-pressure synchrotron diffraction study of ternary and non-stoichiometric PbTe and PbSe crystals	Shchennikov
Tu-P2-63	K. Yamaura, Q. Huang, L. Zhang, K. Takada, Y. Baba, T. Nagai	Spinel-to-CaFe <sub>2</sub> O <sub>4</sub> type structural transformation in LiMn <sub>2</sub> O <sub>4</sub> under high pressure	Yamaura
Tu-P2-64	V. Dyakonov, F.N. Bukhanko, V.I. Kamenev, E E Zubov, M Arcondo	Structural and magnetic phase transitions in La <sub>1-x</sub> Pr <sub>x</sub> MnO <sub>3</sub> manganites under internal and hydrostatic pressure	Dyakonov
Tu-P2-65	S. Lamari	of Electrons in Inversion layers on Narrow Gap Semiconductors	Lamari
Tu-P2-66	A. Misiuk, J. Bak-Misiuk, A. Barcz, W. Osinniy	Properties of Cz-Si:Mn processed under enhanced pressure	Misiuk
Tu-P2-67	J. Pellicer-Porres, J.A. Sans, J.F. Sánchez-Royo, A. Segura, J. Muñoz	Local environment of Mn in Zn <sub>1-x</sub> Mn <sub>x</sub> O probed by x-ray absorption spectroscopy under high pressure	Pellicer-Porres
Tu-P2-68	J.A. Sans, J.F. Sánchez-Royo, J. Pellicer, Ch. Ferrer-Roca, A. Segura	Pressure dependence of the optical properties of wurtzite and rock-salt Zn <sub>1-x</sub> CoxO thin films	Sans
Tu-P2-69	D. Christofilos, J. Arvanitidis, K.S. Andrikopoulos, G.A. Kourouk	Comparative high pressure Raman study of isolated and bundled single-wall carbon nanotubes	Christofilos
Tu-P2-70	P.T.C. Freire, V. Lemos, P.S. Pizani, J.A. Lima Jr., R.O. Nascimento	Pressure effects on surfactant solubilized single-wall carbon nanotubes	Freire
Tu-P2-71	S. Guerini, V. Lemos, P. Piquini, S.S. Coutinho	Energetic and electronic properties BN nanotube bundle under pressure	Guerini
Tu-P2-72	H.M. Guyvan, V.M. Kedyulich, A.G. Slivka, E.I. Gerzanich	Effect of uniaxial stress of various symmetry on the dielectric properties of Rochelle Salt crystals	Guyvan

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Tu-P2-73	K. Hild, S.J. Sweeney, I. P. Marko, S.R. Jin	Temperature and Pressure Dependence of Carrier Recombination processes in GaAsSb/GaAs Quantum Well Lasers	Hild
Tu-P2-74	R.S. Kumar, A.L. Cornelius, M.F. Nicol	Equation of state of nanocrystalline BaTiO <sub>3</sub> upto 52GPa at room temperature	Kumar
Tu-P2-75	K. O'Brien, S. J. Sweeney, A. R. Adams, S. R. Jin, C. N. Ahma	Carrier recombination in mid-infrared GaInAsSb quantum well lasers	O'Brien
Tu-P2-76	K. Papagelis, J. Arvanitidis, D. Christofilos, K.S. Andrikopoulos	Second-order Raman study of double-wall carbon nanotubes under high pressure	Papagelis
Tu-P2-77	D.G. McConville, S.J. Sweeney, A.R. Adams, S. Tomic, H. Ried	The temperature and pressure dependence of carrier recombination processes in 1.3 $\mu$ m and 1.5 $\mu$ m GaInNAs lasers	McConville
Tu-P2-78	I.-H. Choi, P.Y. Yu, P. Tangney, S.G. Louie	Structural Phase Transition in Singlewalled Carbon Nanotubes under High Pressure	Yu
Tu-P2-79	A. Ciungu, B. Buller, B.U. Rao, U.D. Venkateswaran, V. Krungl	Raman scattering and gas adsorption studies on single-walled carbon nanohorns	Venkateswaran
Tu-P2-80	R. Bohdan, M. Wojdak, A. Bercha, F. Dybala, P. Adamiec, W. T	Tuning of the high-brightness tapered laser in the 980 nm – 880 nm range	Bohdan
Tu-P2-81	F. Dybala, A. Bercha, P. Adamiec, R. Bohdan, W. Trzeciakows	Tunable laser in the 1575 nm –1225 nm range achieved by pressure tuning combined with grating tuning	Dybala
Tu-P2-82	K. O'Brien, S.J. Sweeney, A.R. Adams, S.R. Jin, C.N. Ahmad,	High pressure studies of mid-infrared type-II "W" diode lasers at cryogenic temperatures	O'Brien
Tu-P2-83	Z. Dibi, M.L. Hafiane	Artificial Neural Network-Based Hysteresis Estimation of Capacitive Pressure Sensor	Dibi
Tu-P2-84	J. Sjakste, N. Vast, V. Tyuterev	Electronic deexcitation by intervalley scattering: an ab initio study in GaAs and GaP	Sjakste
Tu-P2-85	E. Sterer, I.F. Silvera, P. Shuker	Expanding the limits of TM studies in a laser heated DAC	Sterer
Tu-P2-86	E.G. Villora, K. Shimamura, Kazuo Aoki, K. Kitamura	Effective surface reconstruction of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> substrates above 103 Pa NH <sub>3</sub> for GaN epitaxy	Villora
Tu-P2-87	A. Bercha, O. Mariani, F. Dybala, P. Adamiec, R. Bohdan, W. T	Spectroscopic measurements using pressure-tuned laser diodes	Bercha
Tu-P2-88	N. F. Massé, S. J. Sweeney, A. R. Adams	Experimental study of the pressure dependence of Auger recombination in InGaAs/InP 1.5 $\mu$ m quantum well lasers at room temperature	Massé



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We-8-1i	E.A. Ekimov, V.A. Sidorov, E.D. Bauer, N.N. Mel'nik, J.D. Thom	Superconductivity in diamond induced by boron doping at high-pressure	Ekimov
We-8-2	??????	Pressure Effects and Anisotropic Polarons in Layered MgB <sub>2</sub> Superconductor	Ivanov
We-8-3i	E.M. Dizhur, A.N. Voronovsky, I.N. Kotel'nikov, S.E. Dizhur	Pressure-induced Metal-Insulator Transition of 2D Electron Gas in d-doped GaAs	Dizhur
We-8-4	V.S. Filinov, M. Bonitz, V.E. Fortov, H. Fehske, P. Levashov	Coulomb crystal and quantum melting in electron-hole plasmas of semiconductors under high pressure	Filinov
We-9-1i	J. Arvanitidis, D. Christofilos	High pressure Raman studies of double wall carbon nanotubes	Arvanitidis
We-9-2	J. González, Ch. Power, J.M. Broto, B. Raquet, B. Lassagne, P	Pressure dependence of Raman modes in DWCNT filled with 1D nanocrystalline PbI <sub>2</sub> semiconductor	González
We-9-3	S.B. Fagan, V. Lemos	Ab initio study of double-wall carbon nanotubes under uniaxial pressure	Fagan
We-9-4	J.E. Proctor, M.P. Halsall, D.J. Dunstan, A. Ghambour	High pressure Raman spectroscopy of single-walled carbon nanotubes: Effect of chemical environment on individual nanotubes and the nanotube bundle	Proctor
We-9-5	V. Lemos, S. Guerini, R.F. Abreu, J. Mendes Filho, S.B. Fagan	Interaction of a methanol molecule with C <sub>60</sub> under pressure	Lemos
We-9-6	G.V. Tikhomirova, A.N. Babushkin	Different conductive phases of C <sub>60</sub> induced by high pressures up to 50 Gpa	Tikhomirova
We-10-1i	??????	Magnetoelastic effects in colossal magnetoresistance Pr <sub>1-x</sub> CaxMnO <sub>3</sub> compounds	Remenyi
We-10-2i	??????	Pressure-induced colossal magnetocaloric effect in MnAs	Gama
We-10-3	K. RUPPRECHT, O. LEUPOLD, U. PONKRATZ, G. WORTMA	Magnetic Properties of CsCl-type Eu-Monochalcogenides at Extreme Pressures	Wortmann
We-11-2i	??????	Femtosecond pump & probe spectroscopy in Bi under pressure	Mishina
Th-11-3i	I.F. Silvera	Calibration of the Ruby Pressure Scale to 150 GPa	Silvera
Th-11-4i	M. Gauthier, F. Decremps	Ultrasonic measurements under high pressure	Gauthier



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Th-12-1	D. Errandonea, J. Pellicer-Porres, F.J. Manjón, N. Garro, A. Se	Crystal stability and pressure-induced phase transitions in scheelite $\text{CaWO}_4$ and isostructural $\text{AWO}_4$ ( $A = \text{Sr}, \text{Ba}, \text{Pb}, \text{Eu}$ ) binary oxides: A Review of recent ADXRD, XANES, Raman and ab-initio studies	Manjón
Th-12-2	K. Matsuishi, S. Umeda, D. Kakuta, S. Onari, S. Nakano, K. Ta	Hydrostatic pressure effects on structural and electronic properties of inorganic-organic perovskite semiconductor $(\text{CH}_3\text{NH}_3)\text{PbBr}_3$	Matsuishi
Th-12-3	K. Shirai, A. Masago, H. Katayama-Yoshida	High-pressure properties and phase diagram of boron	Shirai
Th-12-4	A. Polian, J.C. Chervin, P. Munsch, M. Gauthier	a-boron under high pressure: new results	Polian
Th-12-5i	A. Goncharov	Optical, Vibrational and Elastic Properties of Materials under Extreme Conditions	Goncharov